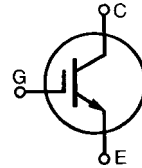


# HiPerFAST™ IGBT Lightspeed™ Series

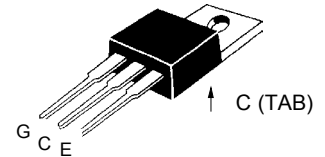
**IXGA 24N60C**  
**IXGP 24N60C**

**V<sub>CES</sub> = 600 V**  
**I<sub>C25</sub> = 48 A**  
**V<sub>CE(sat)typ</sub> = 2.1 V**  
**t<sub>fi typ</sub> = 60 ns**

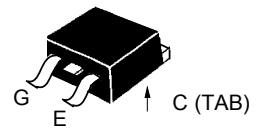


Symbol	Test Conditions	Maximum Ratings	
V <sub>CES</sub>	T <sub>J</sub> = 25°C to 150°C	600	V
V <sub>CGR</sub>	T <sub>J</sub> = 25°C to 150°C; R <sub>GE</sub> = 1 MΩ	600	V
V <sub>GES</sub>	Continuous	±20	V
V <sub>GEM</sub>	Transient	±30	V
I <sub>C25</sub>	T <sub>C</sub> = 25°C	48	A
I <sub>C110</sub>	T <sub>C</sub> = 110°C	24	A
I <sub>CM</sub>	T <sub>C</sub> = 25°C, 1 ms	96	A
<b>SSOA (RBSOA)</b>	V <sub>GE</sub> = 15 V, T <sub>VJ</sub> = 125°C, R <sub>G</sub> = 22 Ω Clamped inductive load, L = 100 μH	I <sub>CM</sub> = 48 @ 0.8 V <sub>CES</sub>	A
P <sub>C</sub>	T <sub>C</sub> = 25°C	150	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	°C
M <sub>d</sub>	Mounting torque (M3)	1.13/10 Nm/lb.in.	
<b>Weight</b>		TO-263	2 g
		TO-220	4 g

## TO-220 AB (IXGP)



## TO-263 AA (IXGA)



G = Gate, C = Collector,  
E = Emitter, TAB = Collector

## Features

- International standard packages JEDEC TO-247 and surface mountable TO-268
- High frequency IGBT
- High current handling capability
- Latest generation HDMOS™ process
- MOS Gate turn-on - drive simplicity

## Applications

- PFC circuits
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

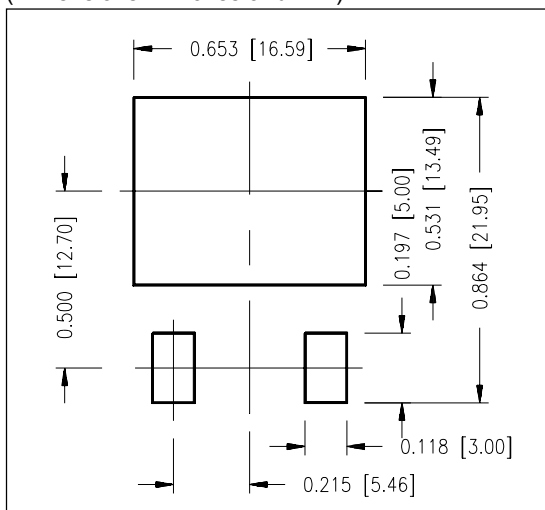
## Advantages

- High power density
- Very fast switching speeds for high frequency applications

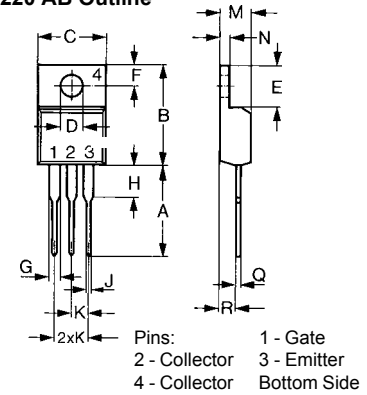
Symbol	Test Conditions	Characteristic Values (T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
BV <sub>CES</sub>	I <sub>C</sub> = 250 μA, V <sub>GE</sub> = 0 V	600		V
V <sub>GE(th)</sub>	I <sub>C</sub> = 250 μA, V <sub>CE</sub> = V <sub>GE</sub>	2.5		5 V
I <sub>CES</sub>	V <sub>CE</sub> = 0.8 • V <sub>CES</sub> V <sub>GE</sub> = 0 V			T <sub>J</sub> = 25°C: 200 μA T <sub>J</sub> = 150°C: 1 mA
I <sub>GES</sub>	V <sub>CE</sub> = 0 V, V <sub>GE</sub> = ±20 V			±100 nA
V <sub>CE(sat)</sub>	I <sub>C</sub> = I <sub>C110</sub> , V <sub>GE</sub> = 15 V	2.1	2.5	V

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$g_{fs}$	$I_C = I_{C110}$ ; $V_{CE} = 10\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $\leq 2\%$	9	17	S	
$C_{ies}$	$V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$ , $f = 1\text{ MHz}$		1500	pF	
$C_{oes}$			120	pF	
$C_{res}$			40	pF	
$Q_g$	$I_C = I_{C110}$ , $V_{GE} = 15\text{ V}$ , $V_{CE} = 0.5 V_{CES}$		55	nC	
$Q_{ge}$			13	nC	
$Q_{gc}$			17	nC	
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = I_{C110}$ , $V_{GE} = 15\text{ V}$ , $L = 100\ \mu\text{H}$ , $V_{CE} = 0.8 V_{CES}$ , $R_G = R_{off} = 10\ \Omega$ Remarks: Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		15	ns	
$t_{ri}$			25	ns	
$t_{d(off)}$			75	140	ns
$t_{fi}$			60	110	ns
$E_{off}$			0.24	0.36	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = I_{C110}$ , $V_{GE} = 15\text{ V}$ , $L = 100\ \mu\text{H}$ , $V_{CE} = 0.8 V_{CES}$ , $R_G = R_{off} = 10\ \Omega$ Remarks: Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		15	ns	
$t_{ri}$			25	ns	
$E_{on}$			0.15	mJ	
$t_{d(off)}$			130	ns	
$t_{fi}$			110	ns	
$E_{off}$		0.6	mJ		
$R_{thJC}$			0.83	K/W	
$R_{thCK}$		0.25		K/W	

### Min. Recommended Footprint (Dimensions in inches and mm)

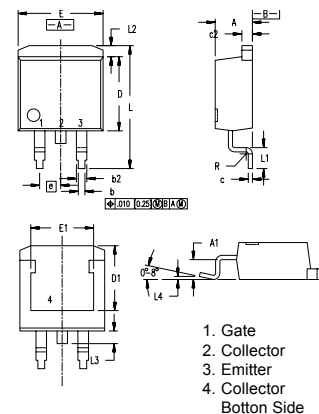


### TO-220 AB Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.35	0.56	0.014	0.022
R	2.29	2.79	0.090	0.110

### TO-263 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.06	4.83	.160	.190
A1	2.03	2.79	.080	.110
b	0.51	0.99	.020	.039
b2	1.14	1.40	.045	.055
c	0.46	0.74	.018	.029
c2	1.14	1.40	.045	.055
D	8.64	9.65	.340	.380
D1	7.11	8.13	.280	.320
E	9.65	10.29	.380	.405
E1	6.86	8.13	.270	.320
e	2.54	BSC	.100	BSC
L	14.61	15.88	.575	.625
L1	2.29	2.79	.090	.110
L2	1.02	1.40	.040	.055
L3	1.27	1.78	.050	.070
L4	0	0.38	0	.015
R	0.46	0.74	.018	.029

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1  
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025